



#### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
	20mΩ @ V <sub>GS</sub> = 10V	6.9A
30V	27mΩ @ V <sub>GS</sub> = 4.5V	5.8A

#### **Description**

This MOSFET has been designed to minimize the on-state resistance  $(R_{DS(on)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

#### **Applications**

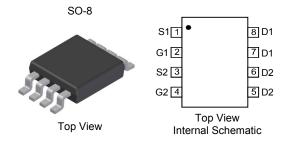
- Backlighting
- Power Management Functions
- DC-DC Converters

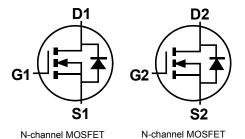
#### **Features**

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper lead frame.
   Solderable per MIL-STD-202, Method 208
- Weight: 0.072grams (approximate)





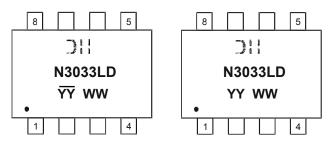
## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3033LSD-13	SO-8	2,500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

# **Marking Information**



Shanghai A/T Site

□ | = Manufacturer's Marking
N3033LD = Product Type Marking Code
YYWW = Date Code Marking
YY or \( \overline{YY} = Year \) (ex: 13 = 2013)
WW = Week (01 - 53)
YY = Date Code Marking for SAT (Shanghai Assembly/ Test site)
\( \overline{YY} = Date Code Marking for CAT \) (Chengdu Assembly/ Test site)

Chengdu A/T Site



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Drain Current (Note 5)	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	6.9 5.8	А
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	30	Α

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_{D}$	2	W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62.5	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

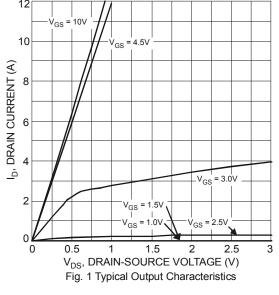
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

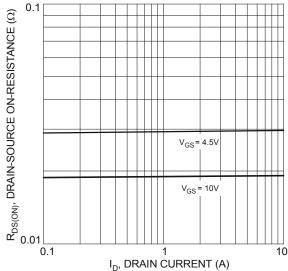
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	100	nA	$V_{DS} = 30V, V_{GS} = 0V$	
Cata Sauraa Laakaga	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
Gate-Source Leakage		_	_	1	μA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	1	l	2.1	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	J		13	20	mΩ	$V_{GS} = 10V, I_D = 6.9A$	
Static Dialit-Source Off-Resistance	R <sub>DS (ON)</sub>	_	22	27	11122	$V_{GS} = 4.5V, I_D = 5A$	
Forward Transconductance	g <sub>fs</sub>	_	7	_	S	$V_{DS} = 5V, I_D = 6.9A$	
Diode Forward Voltage (Note 7)	$V_{SD}$	0.5	_	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C <sub>iss</sub>		725	_	pF	45)/ )/ 0)/	
Output Capacitance	Coss	_	114	_	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V -f = 1MHz	
Reverse Transfer Capacitance	$C_{rss}$		92	_	pF	1 - 1101112	
Gate Resistance	$R_{G}$	_	0.89	_	Ω	$V_{GS} = 0V$ , $V_{DS} = 0V$ , $f = 1MHz$	
SWITCHING CHARACTERISTICS							
Total Gate Charge	Qg	_	6.4 13	_	nC	$V_{GS} = 4.5V, V_{DS} = 15V, I_{D} = 5A$	
Total Gate Charge						$V_{GS} = 10V, V_{DS} = 15V, I_D = 6.9A$	
Gate-Source Charge	$Q_{gs}$		1.9	_	nC	$V_{GS} = 4.5V, V_{DS} = 15V, I_D = 6.9A$	
Gate-Drain Charge	$Q_{gd}$		3.2	_	nC	$V_{GS} = 4.5V, V_{DS} = 15V, I_D = 6.9A$	
Turn-On Delay Time	t <sub>d(on)</sub>		11	_	ns		
Turn-On Rise Time	t <sub>r</sub>	_	7	_	ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V,	
Turn-Off Delay Time	t <sub>d(off)</sub>	_	63	_	ns	$R_D = 1.8\Omega$ , $R_G = 6\Omega$	
Turn-Off Fall Time	t <sub>f</sub>		30	_	ns		

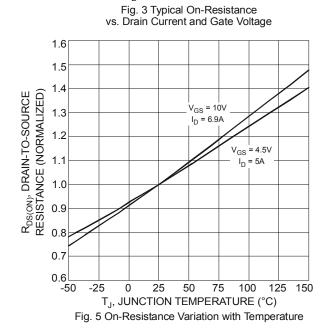
5. Device mounted on 2 oz. Copper pads on FR-4 PCB with  $R_{\theta JA}$  = 62.5°C/W Notes:

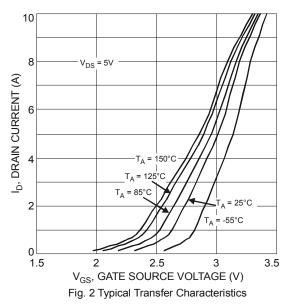
6. Pulse width ≤10µS, Duty Cycle ≤1%.
7. Short duration pulse test used to minimize self-heating effect.











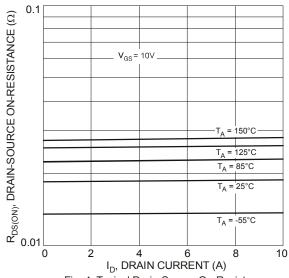
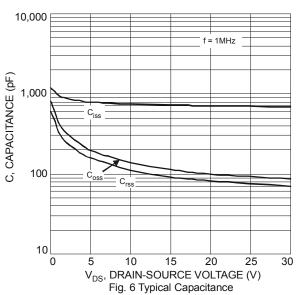


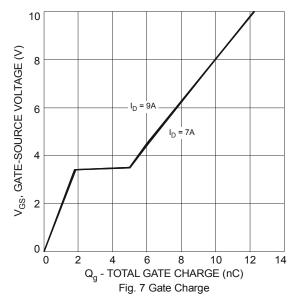
Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

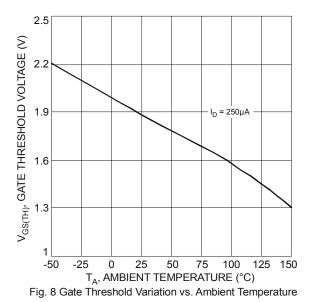


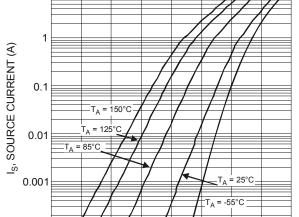


10

0.0001







V<sub>SD</sub>, SOURCE-DRAIN VOLTAGE (V) Fig. 9 Diode Forward Voltage vs. Current

0.5

0.4

0.6

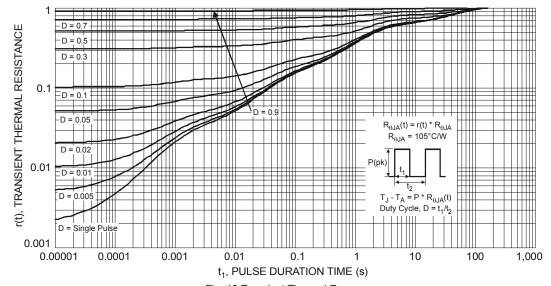
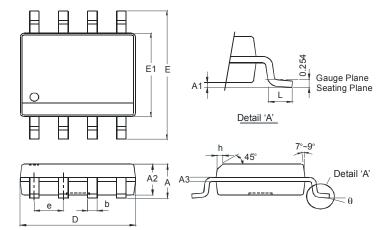


Fig. 10 Transient Thermal Response



# **Package Outline Dimensions**

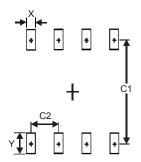
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SO-8					
Dim	Min	Max			
Α	-	1.75			
<b>A</b> 1	0.10	0.20			
A2	1.30	1.50			
A3	0.15	0.25			
b	0.3	0.5			
D	4.85	4.95			
Е	5.90	6.10			
E1	3.85	3.95			
е	1.27 Typ				
h	1	0.35			
L	0.62	0.82			
θ	0°	8°			
All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27



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